#### **ECH8672**

## ON Semiconductor®

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### P-Channel Power MOSFET -20V, -3.5A, 85mΩ, Dual ECH8

#### **Features**

- 1.8V drive
- · Composite type, facilitating high-density mounting
- · Halogen free compliance

#### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

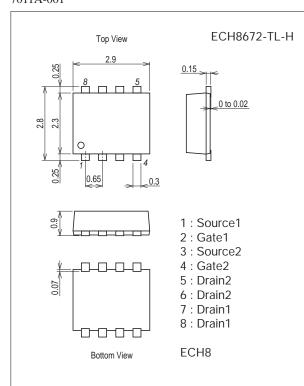
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-20	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		-3.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-30	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm <sup>2</sup> ×0.8mm) 1unit	1.3	W
Total Power Dissipation	PT	When mounted on ceramic substrate (1200mm <sup>2</sup> ×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity < 200V\*", so please take care when handling.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### **Package Dimensions**

unit : mm (typ) 7011A-001



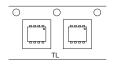
#### **Product & Package Information**

• Package : ECH8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

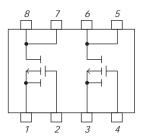
#### Packing Type: TL



#### Marking



#### **Electrical Connection**

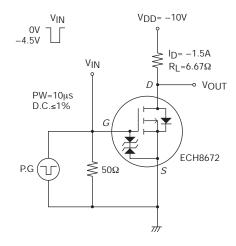


<sup>\*</sup> Machine Model

#### Electrical Characteristics at Ta=25°C

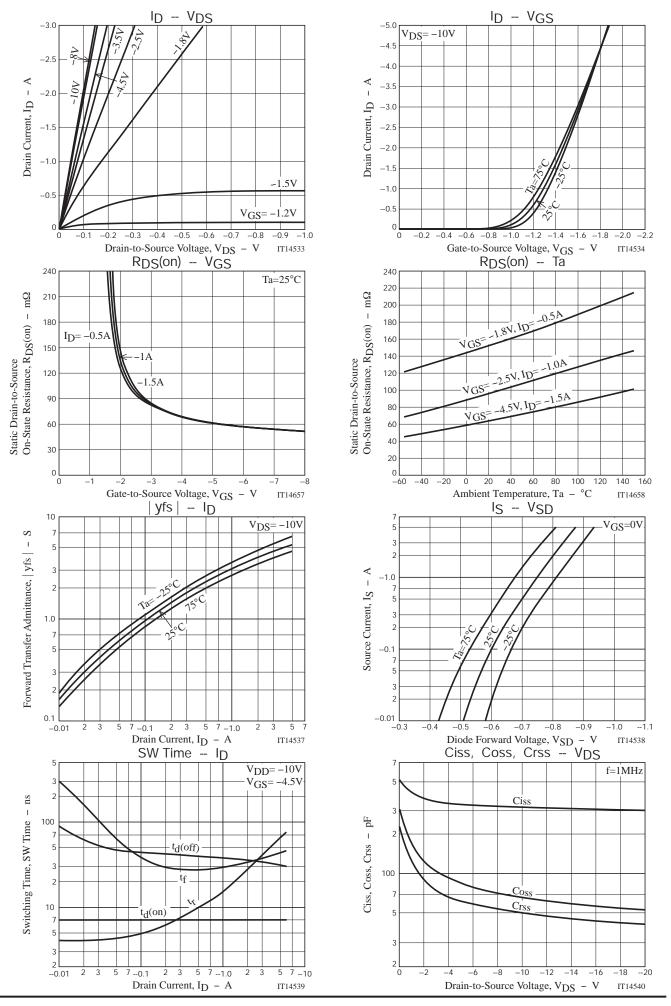
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Offic	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-20			V	
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V			-1	μΑ	
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ	
Cutoff Voltage	V <sub>GS</sub> (off)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-0.4		-1.3	V	
Forward Transfer Admittance	yfs	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1.5A 2.1		3.6		S	
	R <sub>DS</sub> (on)1	I <sub>D</sub> =-1.5A, V <sub>GS</sub> =-4.5V	<sub>y=-1.5</sub> A, V <sub>GS</sub> =-4.5V		85	mΩ	
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)2	I <sub>D</sub> =-1A, V <sub>GS</sub> =-2.5V		98	137	mΩ	
	R <sub>DS</sub> (on)3	I <sub>D</sub> =-0.5A, V <sub>G</sub> S=-1.8V	155		235	mΩ	
Input Capacitance	Ciss			320		pF	
Output Capacitance	Coss	V <sub>DS</sub> =-10V, f=1MHz		66		pF	
Reverse Transfer Capacitance	Crss			50		pF	
Turn-ON Delay Time	t <sub>d</sub> (on)			7.1		ns	
Rise Time	t <sub>r</sub>	See specified Test Circuit.		21		ns	
Turn-OFF Delay Time	t <sub>d</sub> (off)			37		ns	
Fall Time	t <sub>f</sub>			32		ns	
Total Gate Charge	Qg			4.0		nC	
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.5A		0.6		nC	
Gate-to-Drain "Miller" Charge	Qgd	_		1.1		nC	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-3.5A, V <sub>G</sub> S=0V		-0.84	-1.2	V	

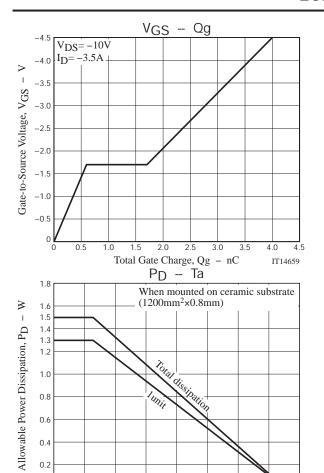
#### Switching Time Test Circuit



#### **Ordering Information**

Device	Package	Shipping	memo		
ECH8672-TL-H ECH8		3,000pcs./reel	Pb Free and Halogen Free		





40 60 80 100 120 Ambient Temperature, Ta - °C

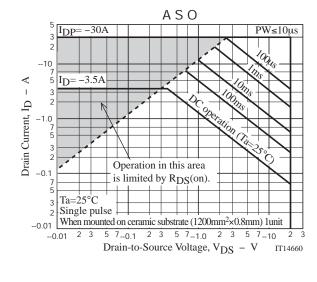
160

140 IT14661

0.2 0

0

20

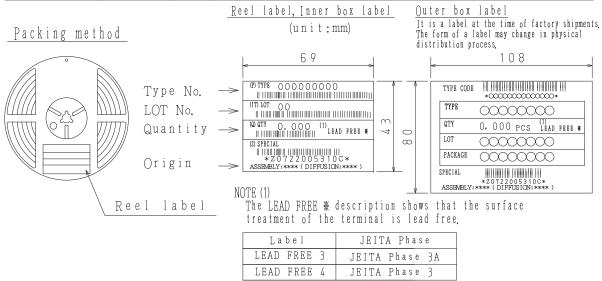


#### **Embossed Taping Specification**

#### ECH8672-TL-H

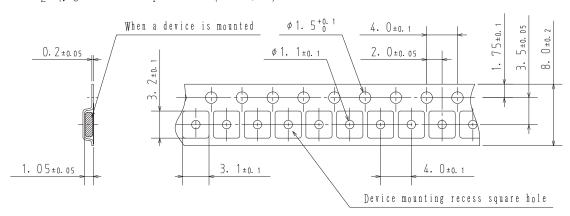
#### 1. Packing Format

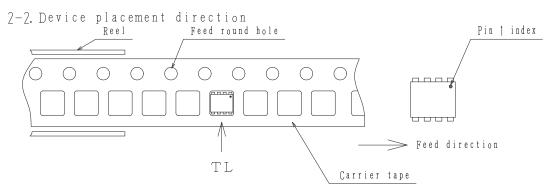
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
	Туре	Reel	Inner box	Outer box	Inner $BOX(C-1)$	Outer BOX (A-7)	
ECH8	СРН6	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained	
					Dimensions:mm (external)	Dimensions:mm (external)	
					183×72×185	440×195×210	



#### 2. Taping configuration

2-1. Carrier tape size (unit:mm)





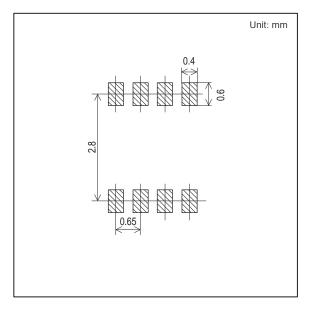
Those with pin 1 index on the feed hole side · · · · · TL

#### **Outline Drawing**

ECH8672-TL-H

# Mass (g) Unit 0.02 mm 2. 9±0.06 7 6 5 LOT No. PIN#1 2. 9±0.05 3. 15-16.15 2. 9±0.05 3. 15-16.15 3. 1

#### Land Pattern Example



Note on usage: Since the ECH8672 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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